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# PHASE IDENTIFICATION IN THE U-SI SYSTEM

by

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Chalk River, Ontario

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#### ABSTRACT

Eight phases (U,  $U_3Si$ ,  $U_3Si_2$ , USi,  $U_2Si_3$ , USi<sub>2</sub>, USi<sub>3</sub> and Si) are reported to occur in the uraniumsilicon system. This report describes the preparation of samples corresponding in composition to these phases, and the identification of each phase using the electron microprobe. The phases were characterized with respect to distribution, etching behaviour and microhardness. The results permit identification of the phases without using the electron microprobe.

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### Identification des phases dans le système U-Si

par L.C. Berthiaume

### Résumé

Huit phases (U,  $U_3Si$ ,  $U_3Si_2$ , USi,  $U_2Si_3$ , USi<sub>2</sub>, USi<sub>3</sub> et Si) se produisent dans le système uranium-silicium. Le présent rapport décrit la préparation des échantillons dont la composition correspond à ces phases et l'identification de chaque phase au moyen de la microsonde électronique. Les phases ont été caractérisées en fonction de la distribution, du comportement sous attaque et de la microdureté. Les résultats permettent d'identifier les phases sans employer la microsonde électronique.

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#### 1. INTRODUCTION

Six intermetallic compounds are reported<sup>(1)</sup> to occur in the uranium silicon system (Figure 1). Although interest in uranium silicon alloys as nuclear fuels is limited to those containing less than 5 wt% silicon, phases of higher silicon content might be encountered due to heterogeneity in castings, selective corrosion, etc. As an aid in identifying such phases, test melts of a range of silicon concentration were prepared and subjected to chemical analysis, metallographic and microprobe examination and microhardness determination.

The results of this study are reported here and a guide to identify the phases suggested.

#### 2. SPECIMEN PREPARATION

Six buttons, of compositions corresponding to each of the phases U3Si, U3Si2, USi, U2Si3 (sometimes referred to (1) as  $\beta$ -USi<sub>2</sub>), USi<sub>2</sub>, USi<sub>3</sub>, were melted under  $\approx 400$  Torr of argon in an arc furnace, equipped with a water-cooled copper hearth. The charge consisted of U<sub>3</sub>Si material prepared by Eldorado Nuclear Ltd.<sup>(2)</sup> with added amounts of elemental silicon when necessary. A second button corresponding to the USi2 composition was subsequently cast by the same method.

All buttons were melted six times, being turned over after each melt, to ensure homogeneity. Button 2 (Table 1) corresponding to the U<sub>3</sub>Si composition was heated at 800°C for 72 hours to form the U<sub>3</sub>Si phase from the as-cast  $(U_3Si_2 + U)$  phases. The remaining buttons were examined in the as-cast condition. In an attempt to obtain the USi<sub>2</sub> phase, one part of button 6A was heat treated at 1300°C for 12 hours while a second part was remelted in a resistance furnace, under vacuum, at 1750°C, cooled to 1500°C, held at that temperature for 2 hours and cooled slowly. The nominal compositions of all buttons, together with their analyzed compositions<sup>(3)</sup> are given in Table 1. Here a ferril Art sector in T

#### 3. METALLOGRAPHIC EXAMINATION

Representative microstructures of samples of each button are given in Figures 2 to 7. The samples were polished mechanically using as last stage a  $\frac{1}{4} \mu m$ diamond paste, then attack-polished with a mixture of a 30% solution of H<sub>2</sub>O<sub>2</sub> and Cr<sub>2</sub>O<sub>3</sub> (produced by igniting (NH<sub>4</sub>)<sub>2</sub> Cr<sub>2</sub>O<sub>7</sub>). The surface of the U<sub>3</sub>Si sample was etched in Murakami's reagent for 75 seconds; the surface of the other alloys was not attacked consistently by this reagent. An etchant<sup>(4)</sup>, employed to reveal grain boundaries in U<sub>3</sub>Si, consisting of 3.4 g citric acid, 72 cm<sup>3</sup> concentrated nitric acid, 1 cm<sup>3</sup> 48% hydrofluoric acid and 170 cm<sup>3</sup> water for 2 to 5 seconds, was used to provide phase contrast in alloys having higher silicon concentration.

None of the buttons was of stoichiometric composition. Two principal phases were observed in each structure.

#### 4. MICROPROBE EXAMINATION

Microprobe analysis permits quantitative determination of elements in each phase in a sample, and thus allows identification of phases observed metallographically.

Using optimized conditions, and pure silicon and uranium standards, precision counts were made (5,6)at several points on each phase in each button. No corrections were made for absorption and atomic difference effect. The results are given in Table 1 and the phases are identified on the metallographic structures shown in Figures 2 to 7. Evidence of the USi<sub>2</sub> phase was found only after the second USi<sub>2</sub> sample was heat treated at 1300°C for 12 hours or cooled slowly after melting in a resistance furnace. Sample 6B was part of a section which separated from the main USi<sub>2</sub> button (6A) during arc melting; this sample was examined because of its major USi phase. Sample 6C was part of sample 6A showing segregation of two phases, USi<sub>3</sub> and USi.

#### 5. MICROHARDNESS

Microhardness measurements were done on all the phases and on uranium and silicon samples using a diamond pyramid hardness identor (136°) under 50, 100 and 200 g loads and using the 50X objective in the Tukon hardness tester. The results are given in Table 2 in relation to the phases identified using the microprobe and metallography techniques. At least ten hardness readings were taken on each phase. A recognizable variation exists between some of the phases, permitting identification of the phases by their hardness. The average hardness values of each phase, when taken under a 200 g load, are given below and plotted in Figure 8. The values taken were those determined when the phases were in major concentration, except for the USi<sub>2</sub> phase which was never observed as the major phase.

i navi	<u>DPHN (20</u>	<u>)0 q)</u>	ini da la	1997 - 19
U		U2Si3	- 850	Çiri (Alisa
U <sub>3</sub> Si	- 244	USi2	- 726,	647
U <sub>3</sub> Si <sub>2</sub>	- 626 de la	USi3	- 415	•
USi	- 701	Si	- 1052	

#### 6. DISCUSSION

No single phase alloy was produced since the intended compositions were not obtained accurately in any of the samples. In general however, the phases identified and the volume fraction of each phase present corresponded roughly to those expected from the phase diagram at the analysed silicon concentration in each sample.

In addition to the microprobe analysis three avenues are open to identify the different phases occurring in a sample; 1) reaction to etching, 2) phase distribution, and 3) hardness of the phases.

#### Etching Behaviour

Although  $U_3Si$  was the only phase which was attacked consistently by Murakami's reagent, some samples of  $USi_2$  developed a tan coloration in this etchant. Thus an unambiguous identification of  $U_3Si$ by this method is not possible.

In all specimens, the phase higher in silicon exhibited a lighter shade after etching in the grain boundary etchant, thus permitting the relative silicon concentrations of the phases present to be identified.

#### Phase Distribution

The USi phase can be identified by its characteristic morphology when present as a minor constituent with the  $U_3Si_2$  phase (Figure 3); such a pattern was observed on samples 3 and 4. The structure of the samples is non-uniform, being hypo-eutectic in some areas and hyper-eutectic in others. In the hypo-eutectic areas the primary USi has precipitated from the melt in a rectilinear growth spiral, illustrating the idiomorphic nature of the compound.

#### Microhardness

A definite variation in hardness exists between most phases. Although the ranges of the measured values overlap, their averages are distinct. The large hardness variation found for phases, when present in major or minor concentration may be attributed to internal stresses or part of the load applied on a minor phase being borne by the major phase. For identification of minor phases a smaller load was generally found to give results more representative of those for a major phase.

Should microprobe analysis not be possible for any reason, the following steps are suggested to identify the phases present in U-Si alloys:

- Determine the hardness of the major phase under a 200 g load on the largest area available and identify possible phases from Table 2. It might be necessary to go to 100 or 50 g load to avoid cracking the harder phases.
- Determine the hardness of the minor phases using a 100 or 50 g load. Identify the possible phases by reference to Table 2 and Figure 8.
- Note metallographically the contrast between the phases, to establish their relative silicon concentrations.

Combination of these observations should identify all the phases unambiguously. Minor inconsistencies in the microhardness values could result from the effect of impurities, heat treatment or cold work.

요즘 물건에 가 물건을 잘 못해 있는 것이 같다.

#### 7. CONCLUSION

The eight phases (U,  $U_3Si$ ,  $U_3Si_2$ , USi,  $U_2Si_3$ , USi<sub>2</sub>, USi<sub>3</sub> and Si) occurring in the uranium-silicon system were observed, identified and hardness tested. No single phase alloy was obtained.

It is possible to identify the phases present in uranium-silicon alloys by a combination of:

- the microhardness of the phases,
- the phase distribution (for USi in U<sub>3</sub>Si<sub>2</sub>),

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- the relatively lighter shade of phases higher in silicon concentration when attacked with a grain boundary etch.

#### 8. ACKNOWLEDGEMENT

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#### 9. **REFERENCES**

 A. Kaufmann, B. Cullity and G. Bitsianes.
"Uranium-Silicon Alloys". AIME Trans. 1957, Vol. 209, p.23; Journal of Metals, January 1957.

2) F.H. Hueston. "The Development of Production Techniques for Uranium Silicide". OPE-42. Eldorado Nuclear Limited, Port Hope, Canada. May 1967. CONF-670522-15 (67-CNA-420)

- 3) R.W. Ashley and P.S. Hardy. "Manual of Methods", section concerned with "Gravimetric Determination of Silicon in Uranium-Silicon Alloys". To be issued as an AECL report.
- 4) J.F.R. Ambler. "Metallographic Evidence for a Martensitic Transformation in U<sub>3</sub>Si". Journal of Nuclear Materials 22, 112-114 (1967).
- 5) J. Baird, private communication.
- 6) Mrs. T. Bethune, private communication.

SILICON, w/o 20 30 50 10 0.5 1 2 1700 (approx) 1700 1665 /L+θ -3000 1610 1600 7 0+L 1575 1570 L+Ś 2800 1510 1500 2600 1+1 1400 L+K 2400 L 1300 ĸ TEMPERATURE,C TEMPERATURE, F L÷e  $\{ f_{i} \} \leq$ 1 7+8 8+1 ί \$+η i+K 1000 985 1800 | γ+€ 930 900 1600 Y+8 -δ+€ 800 -β -β 795 <(U<sub>3</sub> Si<sub>2</sub>) (<sup>5</sup>'s<sup>2</sup>)) ( (USi<sub>s</sub>) <u>(in Si)</u> (sish) -1400 (13<sup>51)</sup> B+8 700 ũ 665 1200  $a + \delta$ 600 -11000 ٠α 500 50 SILICON, a/o 60 70 80 90 100 30 10 20 40 0



- ,7 -







Figure 4

# Sample 6B

500x

Section separated from the main button. Etched in grain boundary etch. Grey - USi - 5; white with dark particles - U-Si mixture.



Figure 5 Sample 5 (14.34 wt% Si) 500x n and  $\zeta$  phases

Etched in grain boundary etch. Grey - USi -  $\zeta$ ; white -  $U_2Si_3 - \eta$ .





Sample 6A, heat-treated at  $1300^{\circ}$ C for 12 hours. Etched in grain boundary etch. Dark grey -  $U_2Si_3 - n$ ; light grey -  $USi_2 - \theta$ ; white -  $USi_3 - i$ .



Figure 7 Sample 7 (29.76 wt% Si) 500x Silicon and  $\iota$  phases Etched in grain boundary etch. Grey - USi<sub>3</sub> -  $\iota$ ; white - silicon rich Si-U mixture.



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## - 12 -

### TABLE 1

## GENERAL DATA SHEET FOR U-Si ALLOYS

Specimen	wt% of Silicon	in Uranium	Microprobe Analysis	Probable Phase	Figure No.
Identity	Intended	Chemical Analysis	Concentration of Silicon in Phases Present (wt%)	Identity	
, <b>1</b>	none (U)				
2	4.0 (U <sub>3</sub> Si)	3.96 (Heat 192)	Major phase - 3.7 Minor phase - 7.3 Residual phase - <0.3	U <sub>3</sub> Si (3.78 wt% Si) U <sub>3</sub> Si <sub>2</sub> (7.29 wt% Si) U	2
са <sub>р</sub> м <b>3</b>	7.27 (U <sub>3</sub> Si <sub>2</sub> )	7.82	Major phase - 7.6 Minor phase - 10.2	U <sub>3</sub> Si <sub>2</sub> (7.29 wt% Si) USi (10.55 wt% Si)	3
. 4	10.53 (USi)	8.78	Major phase - 7.3 Minor phase - 9.9	U <sub>3</sub> Si <sub>2</sub> (7.29 wt% Si) USi (10.55 wt% Si)	
5	15.00 (U <sub>2</sub> Si <sub>3</sub> )	14.34	Major phase - 15.8 Minor phase - 10.3	U <sub>2</sub> Si <sub>3</sub> (15.04 wt% Si) USi (10.55 wt% Si)	5
6		13.7*	50% - phase - 7.4 50% - phase - 10.1	U <sub>3</sub> Si <sub>2</sub> ( 7.29 wt% Si) USi (10.55 wt% Si)	
6A		Í	Major phase - 26.6 Minor phase - 16.3	USi <sub>3</sub> (26.14 wt% Si) U <sub>2</sub> Si <sub>3</sub> (15.04 wt% Si)	
6В			Major phase - 10.1 Minor phase - 1.1	USi (10.55 wt% Si) U-Si mixture	4
60	219.05 (USi <sub>2</sub> )	21.5*	Major phase - 26.9 Minor phase - 10.0	USi <sub>3</sub> (26.14 wt% Si) USi (10.55 wt% Si)	
6D**			Major phase - 25.6 lst Minor phase - 18.6 2nd Minor phase - 16.9	USi <sub>3</sub> (26.14 wt% Si) USi <sub>2</sub> (19.05 wt% Si) U <sub>2</sub> Si <sub>3</sub> (15.04 wt% Si)	6
6F***			lst Minor phase - 33.9	U <sub>3</sub> Si <sub>x</sub> (Eutectic with some USi <sub>3</sub>	
			2nd Minor phase - 20.0 3rd Minor phase - 15.8 4th Minor phase - 15.6	$\begin{array}{c} \text{denarities} \\ \text{USi}_2 & (19.05 \text{ wt\% Si}) \\ \text{U}_2\text{Si}_3 & (15.04 \text{ wt\% Si}) \\ \text{U}_2\text{Si}_3 & (15.04 \text{ wt\% Si}) \end{array}$	
7	26.10 (USi <sub>3</sub> )	29.76	Major phase - 25.6 Minor phase - 95+	USi <sub>3</sub> (26.14 wt% Si) Si-U mixture	7
8	100 (Si)				

\* Silicon concentration obtained by subtraction from U analysis.

\*\* Sample 6A heat treated at 1300°C for 12 hours to give 6D.

\*\*\*

Portion of sample 6A, remelted at 1750°C, held at 1500°C for 2 hours and slowly cooled, to give 6F.

## TABLE 2

MICROHARDNESS OF U-Si PHASES

	Concentration of Phase (Specimen No)	wt% Si in Phase <sup>+</sup>	Microhardness (136° Diamond Pyramid Hardness Numbers)									
Phase Studied			50 g load		100 g load		200 g load			Other Phase(s)		
			Filar Eyepiece Reading		DPHN	Filar Eyepiece Reading		DPHN	Filar Eyepiece Reading		DPHN	Present
		· · ·	Range	Average	Average	Range	Average	Average	Range	Average	Average	
U <sub>3</sub> Si	major (2)	3.7	100-104	101	248	140-150	148	231	199-207	204	244	U <sub>3</sub> Si <sub>2</sub>
U <sub>3</sub> Si <sub>2</sub>	major (3) major (4) minor (2)	7.6	59-62 59-61 65-67	61 60 66	678 701 580*	85-89 80-85 100-110	87 83 106	667 733 450*	125-129 124-125 131-139	127 125 133	626 647 571*	USI USI U <sub>3</sub> SI
USi	major (6B) minor (3) minor (5)	10.1	59-61 58-60 56-61	60 59 58	701 725 750*	83-85 82-84 80-80	84 83 80	717 733 789*	118-120 117-120 110-124	120 118 116	701 726 751*	U-Si mixture U <sub>3</sub> Si <sub>2</sub> U <sub>2</sub> Si <sub>3</sub>
U2Si3	major (5) minor** (6D) minor*** (6F) minor (6A)	15.8	50-56 55-58 54-61 50-56	54 56 57 54	866 805 777* 866	72-78 83-84 83-89 78-81	76 84 86 79	874 717* 683* 809	104-114 no read 121-123 120-120	109 ings (cra 122 120	850 cked) 680* 701*	USI USi <sub>2</sub> and USi <sub>3</sub> USi <sub>2</sub> and USi <sub>3</sub> USi <sub>3</sub>
USi2	minor** (6D) minor*** (6F)	18.6 20.0	58-63 59-60	60 60	701 701	87-92 84-86	89 85	638 700	115-121 124-126	118 125	726 647	$U_2Si_3$ and $USi_3$ $U_2Si_{3+x}$ and $USi_x$
USi3	major (7) major (6A) major (6C) minor** (6D)	25.6	74-75 70-76 74-75 72-74	75 74 74 73	449 461 461 473	110-112 100-120 100-111 101-106	111 111 106 103	410 410 450 476	154-158 148-152 152-160 147-159	156 150 156 153	415 449 415 432	negligible U <sub>2</sub> Si <sub>3</sub> USi USi2 and U <sub>2</sub> Si2
Eutectic + USi3	minor***		60-66	63	637	82-85	84	717	123-126	125	647	U <sub>2</sub> Si <sub>2</sub> and USi <sub>2</sub> *
Si	major (8) minor (7)		50-50 47-53	50 50	1010 1010	70-71 70-71	70 70	1031 1031	95-100 105-108	98 107	1052 883*	none USi3
υ	major (1)		90-90	90	311	125-137	131	294	170-180	175	330	none
U-Si mixture (1.1 wt% Si)	minor		75-77	76	438	93-96	95	560	140-150	145	480	USi

The hardness of these minor phases appears to be influenced by the hardness of the other phases present, at the tested load.

\*\* These samples were heat treated at 1300°C for 12 hours.

\*\*\* These samples were melted at 1750°C, cooled to 1500°C, held at 1500°C for 2 hours and cooled slowly.

+ Determined by microprobe analysis.